

MA3ZD12

Silicon epitaxial planar type

For high-speed switching circuits

■ Features

- S-mini type 3-pin package
- Allowing to rectify under ($I_{F(AV)} = 700$ mA) condition
- Low forward rise voltage V_F ($V_F < 0.45$ V)
- Allowing high-density mounting

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse voltage	V_{RRM}	25	V
Average forward current*2	$I_{F(AV)}$	700	mA
Non-repetitive peak forward surge current*1	I_{FSM}	2	A
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

Note) *1 : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

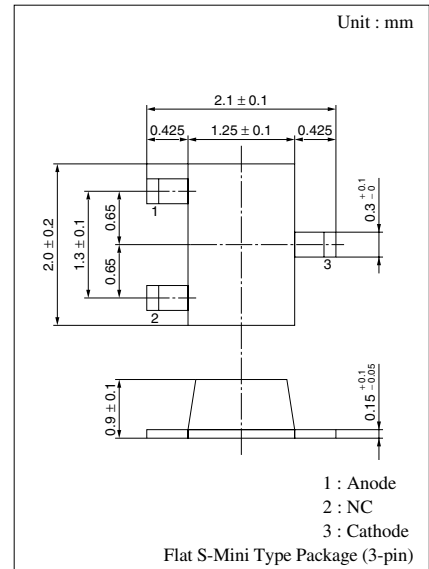
*2 : Mounted on a alumina printed circuit board

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 20$ V			200	μA
Forward voltage (DC)	V_F	$I_F = 700$ mA			0.45	V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		100		pF
Reverse recovery time	t_{rr}	$I_F = I_R = 100$ mA $I_R = 10$ mA, $R_L = 100$ Ω		7		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 250 MHz



Marking Symbol: M5E

Internal Connection

